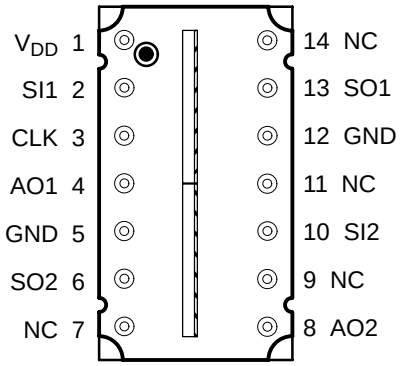
- **256 × 1 Sensor-Element Organization**
- **400 Dots-Per-Inch (DPI) Sensor Pitch**
- **High Linearity and Uniformity**
- **Wide Dynamic Range . . . 4000:1 (72 dB)**
- **Output Referenced to Ground**
- **Low Image Lag . . . 0.5% Typ**
- **Operation to 8 MHz**
- **Single 3-V to 5-V Supply**
- **Rail-to-Rail Output Swing (AO)**
- **No External Load Resistor Required**
- **Replacement for TSL1402**

(TOP VIEW)



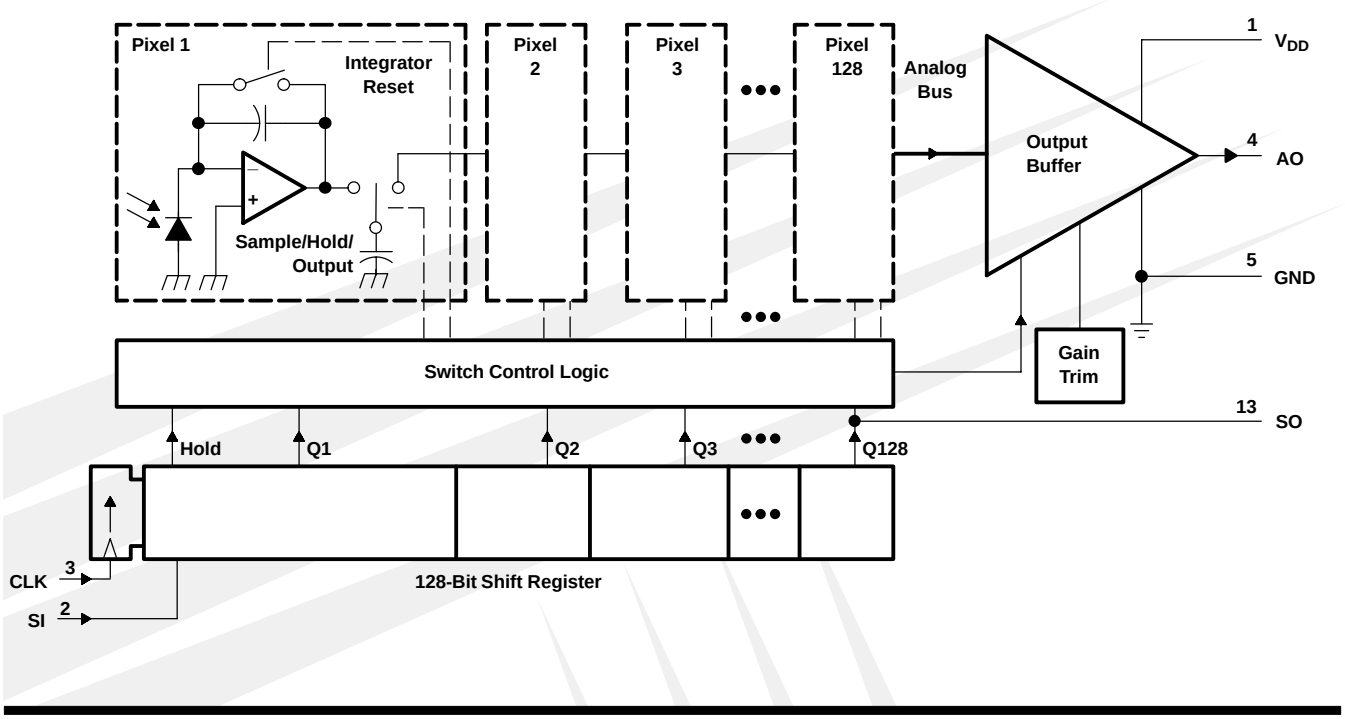
NC − No internal connection

Description

The TSL1402R linear sensor array consists of two sections of 128 photodiodes each and associated charge amplifier circuitry, aligned to form a contiguous 256 × 1 pixel array. The device incorporates a pixel data-hold function that provides simultaneous integration start and stop times for all pixels. The pixels measure 63.5 µm by 55.5 µm, with 63.5-µm center-to-center spacing and 8-µm spacing between pixels. Operation is simplified by internal logic requiring only a serial-input pulse (SI) and a clock.

The TSL1402R is intended for use in a wide variety of applications including mark and code reading, OCR and contact imaging, edge detection and positioning, and optical encoding.

Functional Block Diagram (each section − pin numbers apply to section 1)



Texas Advanced Optoelectronic Solutions Inc.
1001 Klein Road • Suite 300 • Plano, TX 75074 • (972) 673-0759
www.taosinc.com

Terminal Functions

TERMINAL NAME	TERMINAL NO.	DESCRIPTION
AO1	4	Analog output of section 1.
AO2	8	Analog output of section 2.
CLK	3	Clock. Clk controls charge transfer, pixel output, and reset.
GND	5,12	Ground (substrate). All voltages are referenced to GND.
NC	7, 9, 11, 14	No internal connection.
SI1	2	Serial input (section 1). SI1 defines the start of the data-out sequence for section 1.
SI2	10	Serial input (section 2). SI2 defines the start of the data-out sequence for section 2.
SO1	13	Serial output (section 1). SO1 provides a signal to drive the SI2 input (in serial connection).
SO2	6	Serial output (section 2). SO2 provides a signal to drive the SI input of another device for cascading or as an end-of-data indication.
V_{DD}	1	Supply voltage. Supply voltage for both analog and digital circuitry.

Detailed Description

Device operation (assumes serial connection)

The sensor consists of 256 photodiodes, called pixels, arranged in a linear array. Light energy impinging on a pixel generates photocurrent, which is then integrated by the active integration circuitry associated with that pixel.

During the integration period, a sampling capacitor connects to the output of the integrator through an analog switch. The amount of charge accumulated at each pixel is directly proportional to the light intensity on that pixel and the integration time.

The output and reset of the integrators is controlled by a 256-bit shift register and reset logic. An output cycle is initiated by clocking in a logic 1 on SI1. An internal signal, called Hold, is generated from the rising edge of SI1 and simultaneously transmitted to sections 1 and 2. This causes all 256 sampling capacitors to be disconnected from their respective integrators and starts an integrator reset period. As the SI pulse is clocked through the shift register, the charge stored on the sampling capacitors is sequentially connected to a charge-coupled output amplifier that generates a voltage on analog output AO. Simultaneously, during the first 18 clock cycles, all pixel integrators are reset, and the next integration cycle begins on the 19th clock. On the 128th clock rising edge, the SI pulse is clocked out on the SO1 pin (section 1) and becomes the SI pulse for section 2 (SI2). The rising edge of the 129th clock cycle terminates the SO1 pulse, and returns the analog output AO1 of section 1 to high-impedance state. Analog output AO2 now becomes the active output. As in section 2, SO2 is clocked out on the 256th clock pulse. Note that a 257th clock pulse is needed to terminate the SO2 pulse and return AO2 to the high-impedance state. If a minimum integration time is desired, the next SI pulse may be presented after a minimum delay of t_{qt} (pixel charge transfer time) after the 257th clock pulse.

AO is an op amp-type output that does not require an external pull-down resistor. This design allows a rail-to-rail output voltage swing. With V_{DD} = 5 V, the output is nominally 0 V for no light input, 2 V for normal white level, and 4.8 V for saturation light level. When the device is not in the output phase, AO is in a high-impedance state.

The voltage developed at analog output (AO) is given by:

$$V_{out} = V_{drk} + (R_e)(E_e)(t_{int})$$

where:

V_{out}	is the analog output voltage for white condition
V_{drk}	is the analog output voltage for dark condition
R_e	is the device responsivity for a given wavelength of light given in V/(μJ/cm^2)
E_e	is the incident irradiance in μW/cm^2
t_{int}	is integration time in seconds

The TSL1402R can be connected in the serial mode, where it takes 256 clocks to read out all pixels, or in the parallel mode where it takes 128 clocks to read out all pixels (see *APPLICATION INFORMATION* and FIgures 9 and 10).

A 0.1 μF bypass capacitor should be connected between V_{DD} and ground as close as possible to the device.

Absolute Maximum Ratings†

Supply voltage range, V_{DD} . . . . . −0.3 V to 6 V
Input voltage range, V_I . . . . . −0.3 V to V_{DD} + 0.3V
Input clamp current, I_{IK} (V_I < 0) or (V_I > V_{DD}) . . . . . −20 mA to 20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{DD}) . . . . . −25 mA to 25 mA
Voltage range applied to any output in the high impedance or power-off state, V_O . . . −0.3 V to V_{DD} + 0.3 V
Continuous output current, I_O (V_O = 0 to V_{DD}) . . . . . −25 mA to 25 mA
Continuous current through V_{DD} or GND . . . . . −40 mA to 40 mA
Analog output current range, I_O . . . . . −25 mA to 25 mA
Maximum light exposure at 638 nm . . . . . 5 mJ/cm^2
Operating free-air temperature range, T_A . . . . . 0°C to 70°C
Storage temperature range, T_{stg} . . . . . −25°C to 85°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . . 260°C

† Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “Recommended Operating Conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Recommended Operating Conditions (see Figure 1 and Figure 2)

	MIN	NOM	MAX	UNIT
Supply voltage, V_{DD}	3	5	5.5	V
Input voltage, V_I	0		V_{DD}	V
High-level input voltage, V_{IH}	2		V_{DD}	V
Low-level input voltage, V_{IL}	0		0.8	V
Wavelength of light source, λ	400		1000	nm
Clock frequency, f_{clock}	5		8000	kHz
Sensor integration time, Parallel, t_{int} (see Note 1)	0.02375		100	ms
Sensor integration time, Serial, t_{int} (see Note 1)	0.04975		100	ms
Setup time, serial input, $t_{su(SI)}$	20			ns
Hold time, serial input, $t_{h(SI)}$ (see Note 2)	0			ns
Operating free-air temperature, T_A	0		70	°C

NOTES: 1. Integration time is calculated as follows:

t_{int} = (256 − 18) × clock period + 20 μs

where *256* is the number of pixels in series, *18* is the required logic setup clocks, and *20 μs* is the pixel charge transfer time (t_{qt})

2. SI must go low before the rising edge of the next clock pulse.

Electrical Characteristics at f_{clock} = 1 MHz, V_{DD} = 5 V, T_A = 25°C, λ_p = 640 nm, t_{int} = 5 ms, R_L = 330 Ω, E_e = 11 μW/cm² (unless otherwise noted) (see Note 3)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{out}	Analog output voltage (white, average over 256 pixels)	See Note 4	1.6	2	2.4	V
V_{drk}	Analog output voltage (dark, average over 256 pixels)	E_e = 0	0	0.1	0.2	V
PRNU	Pixel response nonuniformity	See Note 5			±10%	
	Nonlinearity of analog output voltage	See Note 6		±0.4%		
	Output noise voltage	See Note 7		1		mVrms
R_e	Responsivity	See Note 8	25	35	45	V/(μJ/cm²)
V_{sat}	Analog output saturation voltage	V_{DD} = 5 V, R_L = 330 Ω	4.5	4.8		V
		V_{DD} = 3 V, R_L = 330 Ω	2.5	2.8		
SE	Saturation exposure	V_{DD} = 5 V, See Note 9		136		nJ/cm²
		V_{DD} = 3 V, See Note 9		78		
DSNU	Dark signal nonuniformity	All pixels, E_e = 0, See Note 10		0.04	0.12	V
IL	Image lag	See Note 11		0.5%		
I_{DD}	Supply current	V_{DD} = 5 V, E_e = 0		6	9	mA
		V_{DD} = 3 V, E_e = 0		5	8	
I_{IH}	High-level input current	$V_I = V_{DD}$			10	μA
I_{IL}	Low-level input current	V_I = 0			10	μA
C_i	Input capacitance, SI			5		pF
C_i	Input capacitance, CLK			10		pF

NOTES: 3. All measurements made with a 0.1 μF capacitor connected between V_{DD} and ground.
4. The array is uniformly illuminated with a diffused LED source having a peak wavelength of 640 nm.
5. PRNU is the maximum difference between the voltage from any single pixel and the average output voltage from all pixels of the device under test when the array is uniformly illuminated at the white irradiance level. PRNU includes DSNU.
6. Nonlinearity is defined as the maximum deviation from a best-fit straight line over the dark-to-white irradiance levels, as a percent of analog output voltage (white).
7. RMS noise is the standard deviation of a single-pixel output under constant illumination as observed over a 5-second period.
8. $R_{e(min)} = [V_{out(min)} - V_{drk(max)}] \div (E_e \times t_{int})$
9. $SE(min) = [V_{sat(min)} - V_{drk(min)}] \times \langle E_e \times t_{int}) \div [V_{out(max)} - V_{drk(min)}]$
10. DSNU is the difference between the maximum and minimum output voltage for all pixels in the absence of illumination.
11. Image lag is a residual signal left in a pixel from a previous exposure. It is defined as a percent of white-level signal remaining after a pixel is exposed to a white condition followed by a dark condition:

$$IL = \frac{V_{out\ (IL)} - V_{drk}}{V_{out\ (white)} - V_{drk}} \times 100$$

Timing Requirements (see Figure 1 and Figure 2)

		MIN	NOM	MAX	UNIT
$t_{su(SI)}$	Setup time, serial input (see Note 12)	20			ns
$t_{h(SI)}$	Hold time, serial input (see Note 12 and Note 13)	0			ns
t_w	Pulse duration, clock high or low	50			ns
t_r, t_f	Input transition (rise and fall) time	0		500	ns
t_{qt}	Pixel charge transfer time	20			μs

NOTES: 12. Input pulses have the following characteristics: t_r = 6 ns, t_f = 6 ns.
13. SI must go low before the rising edge of the next clock pulse.

Dynamic Characteristics over recommended ranges of supply voltage and operating free-air temperature (see Figures 7 and 8)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_s	Analog output settling time to ±1%	R_L = 330 Ω, C_L = 10 pF		120		ns
$t_{pd(SO)}$	Propagation delay time, SO1, SO2			50		ns

TYPICAL CHARACTERISTICS

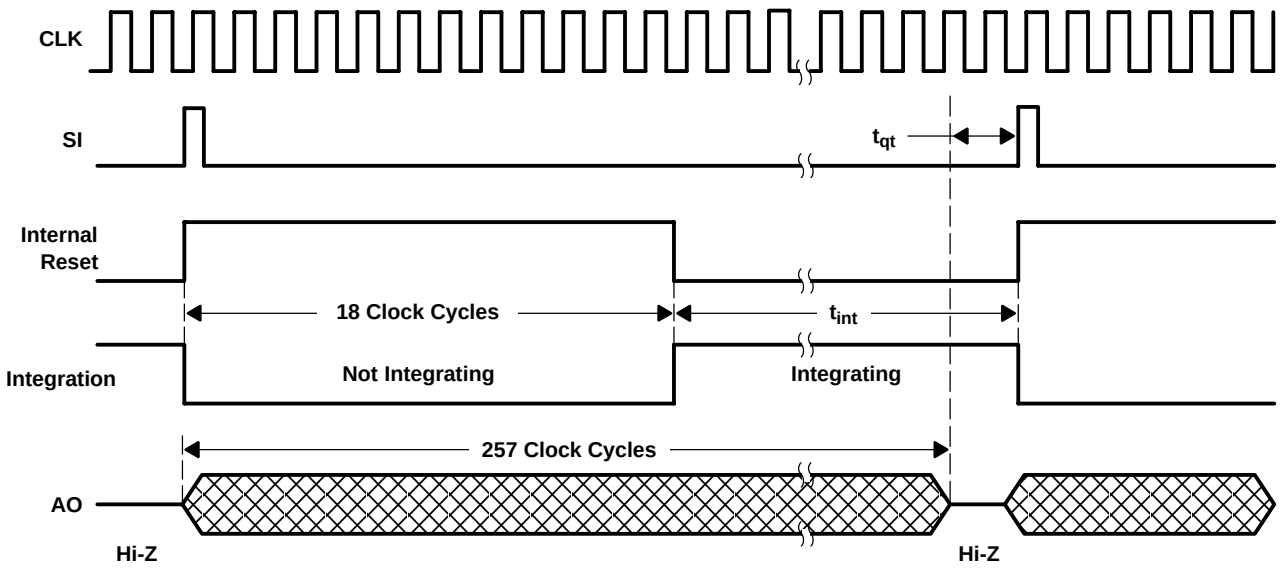


Figure 1. Timing Waveforms (Serial Connection)

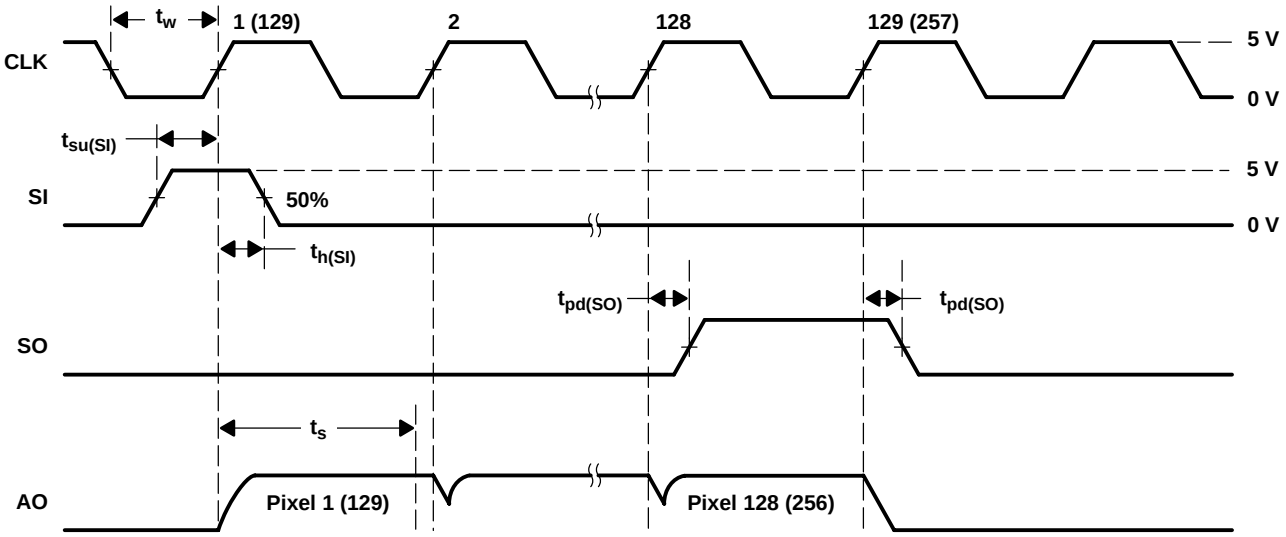


Figure 2. Operational Waveforms (each section)

TYPICAL CHARACTERISTICS

PHOTODIODE SPECTRAL RESPONSIVITY

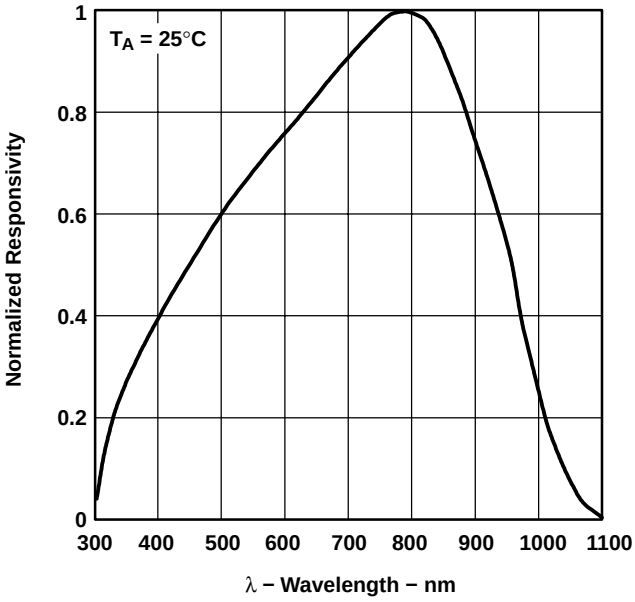


Figure 3

NORMALIZED IDLE SUPPLY CURRENT vs FREE-AIR TEMPERATURE

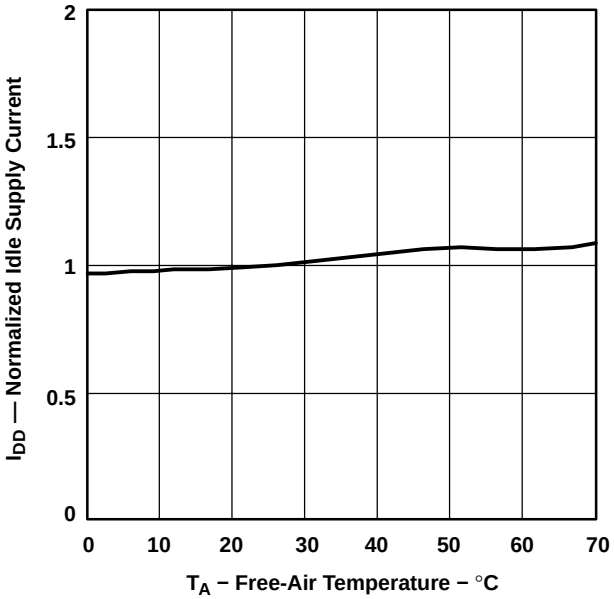


Figure 4

WHITE OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE

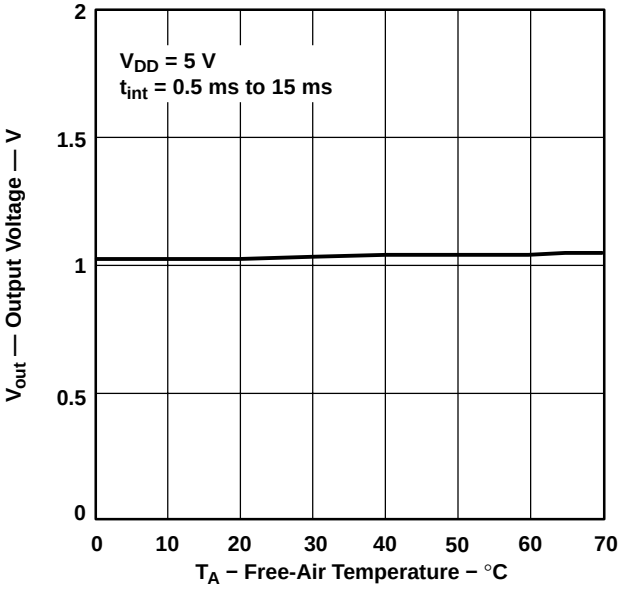


Figure 5

DARK OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE

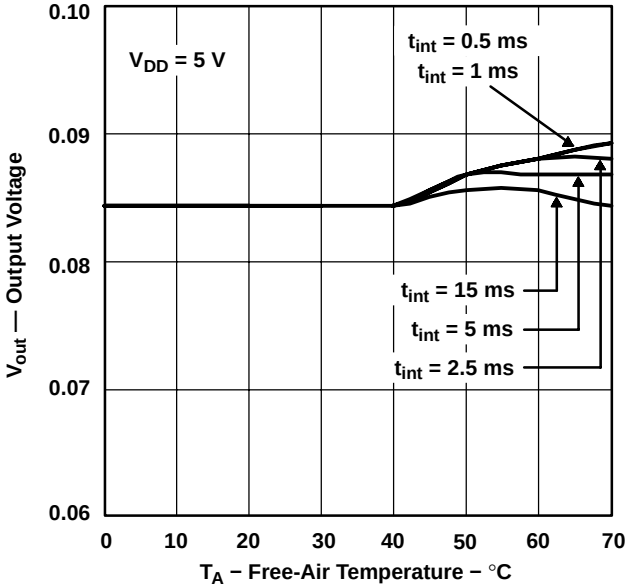


Figure 6

TYPICAL CHARACTERISTICS

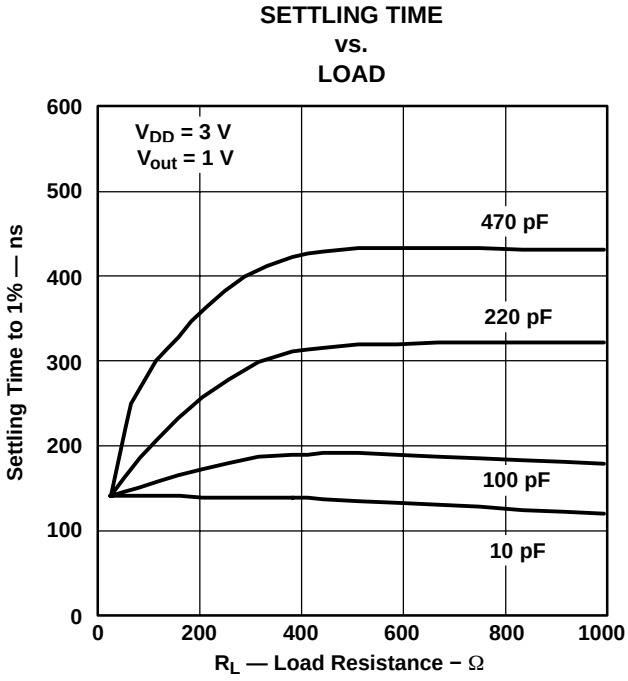


Figure 7

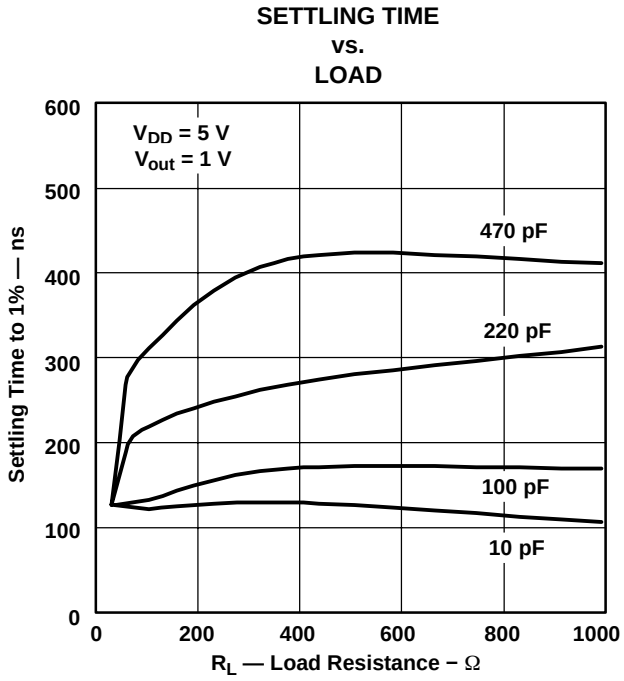


Figure 8

APPLICATION INFORMATION

Power Supply Considerations

For optimum device performance, power-supply lines should be decoupled by a 0.01-μF to 0.1-μF capacitor with short leads mounted close to the device package (see Figure 9 and Figure 10).

Connection Diagrams

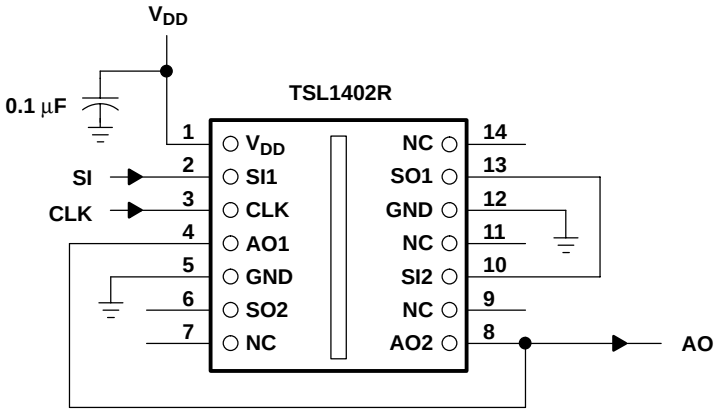


Figure 9. Serial Connection

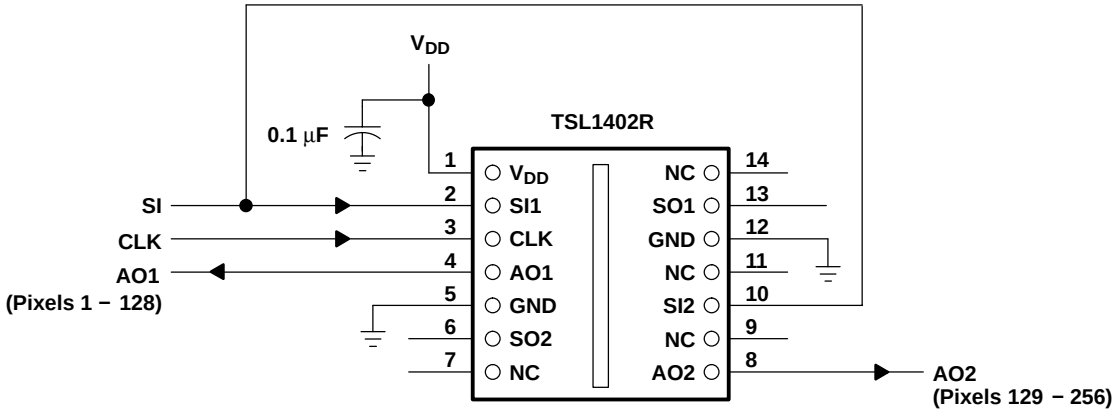
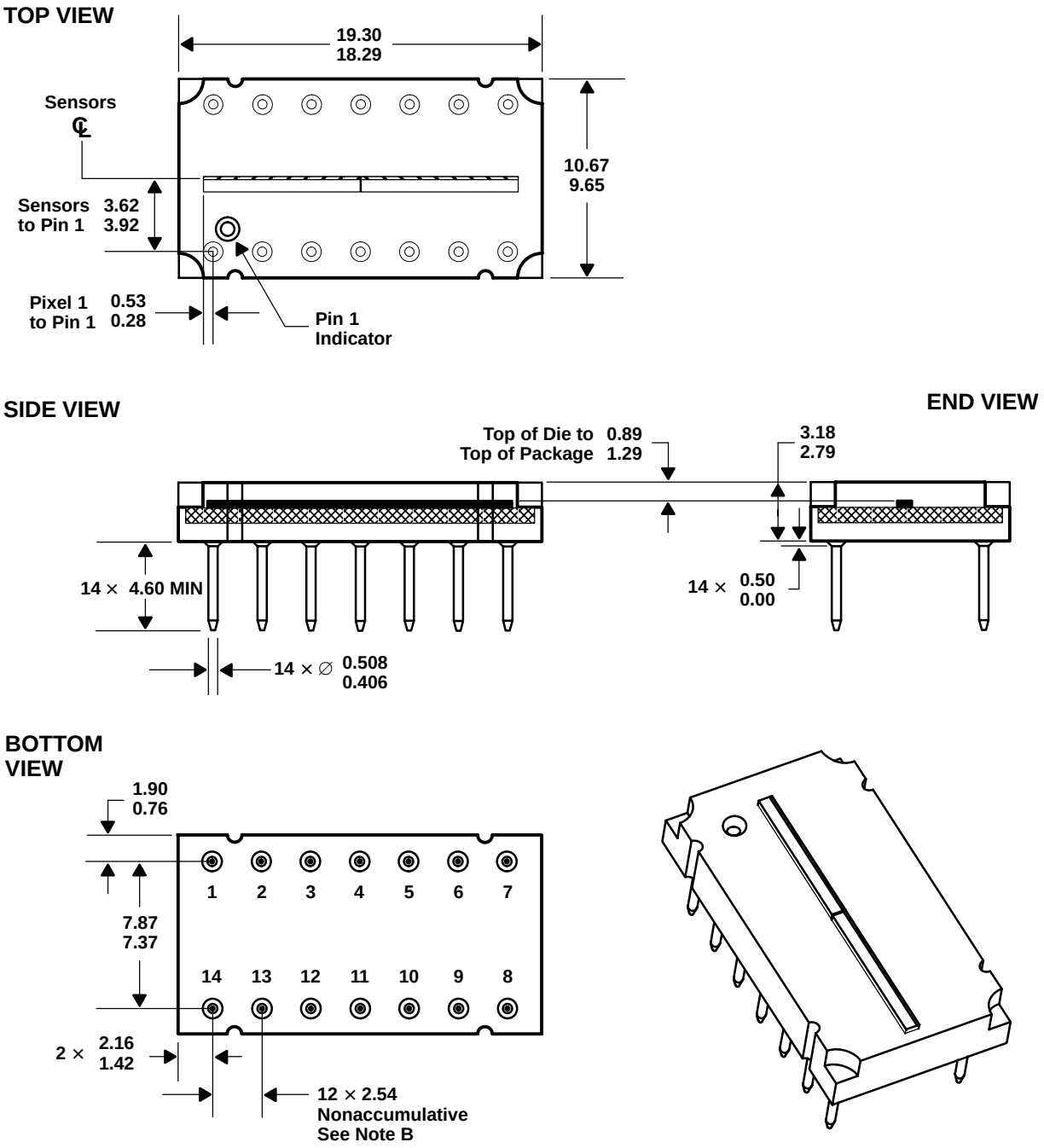


Figure 10. Parallel Connection

MECHANICAL INFORMATION

This assembly consists of 2 sensor chips mounted on a printed-circuit board in a clear molded plastic package.



NOTES: A. All linear dimensions are in millimeters.
B. The true-position spacing is 2.54 mm between lead centerlines. Each pin centerline is located within 0.25 mm of its true longitudinal positions.
C. Index of refraction of clear plastic is 1.52.
D. This drawing is subject to change without notice.

Figure 11. Packaging Configuration

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